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(71)Applicant : FUJITSU LTD

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(54) RADIATION SENSITIVE MATERIAL AND PATTERN FORMING METHOD

(57)Abstract:

PURPOSE: To enable a submicron pattern to be formed in high precision by using a polymer or copolymer of an acrylate or α -substituted acrylate having an adamantan structure in the ester part for a photosensitive material.

CONSTITUTION: The resist pattern is formed by using the radiation sensitive material made of the polymer or copolymer of the acrylate or the α -substituted acrylate having the adamantan structure in the ester part, coating the substrate to be processed, with the obtained resist, and selectively exposing the substrate to radiation, and then developing it, thus permitting the obtained photosensitive material to be enhanced in transparency to the ionizing radiation, to form a resist pattern sufficient in etching resistance, and consequently, to obtain a submicron pattern high in precision.

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